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IMW 2024 TABLE OF CONTENTS

Committees ..... **ix**

Program ..... **xi**

Sponsors ..... **xii**

Session 1: Keynotes

[1.1] Present and Future, Challenges of High Bandwith Memory (HBM) **1**
Kwiwook Kim and Myeong-jae Park

[1.2] Exploring Innovative IGZO-Channel Based DRAM Cell Architectures and Key Technologies for Sub-10nm Node **5**
Daewon Ha, Y. Lee, S. Yoo, W. Lee, M. H. Cho, K. Yoo, S. M. Lee, S. Lee, M. Terai, T. H. Lee, J. H. Bae, K. J. Moon, C. Sung, M. Hong, D. G. Cho, K. Lee, S. W. Park, K. Park, B. J. Kuh, S. Hyun, S. J. Ahn, and J. H. Song

[1.3] Flash Memory Revolution: Journey from 2D to 3D, Migrating to Modular Memory Fabrication **9**
Ryota Katsumata

Session 2: NAND I

[2.1] Pure-Metal Replacement Gate for Reliable 30 nm Pitch Scaled 3D NAND Flash **13**
S. Rachidi, S. Ramesh, D. Tierno, G. L. Donadio, A. Pacco, J. W. Maes, Y. Jeong, A. Arreghini, G. Van den Bosch, and M. Rosmeulen

[2.2] Novel Multi-Level Coding and Architecture Enabling Fast Random Access for Flash Memory **17**
Noboru Shibata, Hironori Uchikawa, Taira Shibuya, and Hirofumi Inoue

[2.3] 3D-NAND Based Filtering Cube with High Resolution 2D Query and Tunable Feature Length for Computational SSD **21**
Po-Hao Tseng, Shao-Yu Fang, Yu-Hsuan Lin, Feng-Ming Lee, Jhe-Yi Liao, Yu-Yu Lin, Ming-Hsiu Lee, Kuang-Yeu Hsieh, Keh-Chung Wang, and Chih-Yuan Lu

Session 3: Ferro/OTS/STT

[3.1] Engineering nvCap from FEOL to BEOL with Ferroelectric Small-Signal Non-Destructive Read **25**
Tae-Hyeon Kim, Yuan-Chun Luo, Omkar Phadke, James Read, and Shimeng Yu

[3.2] AsSeGeS and GeN Heterostructures for Superior OTS Performance **29**
A. Grun, Z. L. Lui, C. W. Cheng, D. Piatek, E. K. Lai, Y. T. Kuo, W. C. Chien, S. Cheng, M. BrightSky, H. L. Lung, and H. Y. Cheng

[3.3] Novel Cross-Point Architecture Utilizing Distributed Diode Selector for Read Margin Amplification **33**
Taras Ravsher, Andrea Fantini, Kruti Trivedi, Nouredine Rassoul, Harold Dekkers, Attilio Belmonte, Jan Van Houdt, Valeri Afanas'ev, Kurt Wostyn, Sebastien Couet, and Gouri Sankar Kar

[3.4] A Novel Test and Analysis Scheme to Elucidate Tail Bit Characteristics in STT-MRAM Arrays **37**
W. Kim, V. Pica, N. Jossart, F. Yasin, K. Wostyn, S. Couet, and S. Rao

Posters Session

[P1] Comprehensive Physics-Based Modeling of Post-Cycling Long-Term Data Retention in 176L 3-D NAND Flash Memories **41**
Karansingh Thakor, Nikhil Rangarajan, Himanshu Diwakar, Rashmi Saikia, Tarun Samadder, Souvik Mahapatra, Shyam Raghunathan, and Yingda Dong

[P2] Embedded Transformer Hetero-CiM: SRAM CiM for 4b Read/Write-MAC Self-Attention and MLC ReRAM CiM for 6b Read-MAC Linear&FC Layers **45**
Naoko Misawa, Tao Wang, Chihiro Matsui, and Ken Takeuchi

[P3] Modeling and Demonstration for Multi-Level Weight Conductance in Computational FeFET Memory Cell **49**
Won-Tae Koo, Jae-Gil Lee, Gunhee Lee, Woocheol Lee, Jungwook Woo, Dong Ik Suh, Joongsik Kim, Hyung Dong Lee, Seho Lee, Jaeyun Yi, and Seon Yong Cha

[P4] Overcome the End of Life of 3D Flash Memory by Recovery Annealing, Aiming for Carbon Neutrality in Semiconductor Manufacturing **53**
Hitomi Tanaka, Hajime Sano, Reika Ichihara, Yuta Aiba, Kazuma Hasegawa, Kana Kudo, Chieko Tokunaga, Yasuhito Yoshimizu, Fumie Kikushima, and Tomoya Sanuki

[P5] High-Efficient and Comprehensive Modeling of MFIM Ferroelectric Tunnel Junctions for Non-Volatile/Volatile Applications **57**
Yu Li, Hao Jiang, Jie Yu, Xuanyu Zhao, Xiaodong Wang, Qihan Liu, Yingfen Wei, Qi Liu, and Ming Liu

[P6] SiGe/Si Heterojunction Drain Transistor for Faster 3D NAND Flash Memory Erase **61**
Dasom Lee and Tsu-Jae King Liu

[P7] Process Optimization and Cryogenic Evaluation of Spin-Orbit Torque Magnetic Random Access Memory **65**
Zhongkui Zhang, Xiaofei Fan, Danrong Xiong, Huiyan Sun, Xiantao Shang, Bowen Man, Cong Zhang, Shuhui Li, Renjie Su, Chengyuan Sun, Jennifer Zhou, Hongxi Liu, and Gefei Wang

[P8] Realistic Noise-Aware Training as a Component of the Holistic ACiM Development Platform **69**
Jihun Kim, Sangsu Park, Hongju Suh, Youngjae Kwon, Seonghun Lee, Yubin Lee, Kayoung Kim, Eungu Han, Jongil Kim, Kyu Sung Kim, Hyejung Choi, Seungwook Ryu, Su Jin Chae, Seho Lee, Soo Gil Kim, Jaeyun Yi, and Seonyong Cha

[P9] A Novel Program-Verify Free and Low Drift Multi-Level Operation on Cross-Point OTS-PCM for In-Memory Computing Application 73
W. C. Chien, C. L. Sung, R. L. Bruce, C. W. Yeh, H. Y. Cheng, Z. L. Liu, E. K. Lai, C. W. Cheng, J. X. Zheng, A. Grun, A. Ray, D. Daudelin, H. Y. Ho, M. BrightSky, and H. L. Lung

[P10] Optimizing RRAM Performance: A Comparative Analysis of Forming Strategies ... 77
Thomas Bauvent, Gaël Pillonnet, and Gabriel Molas

[P11] Understanding the Thermal Aspects in Dense RRAM Memory Arrays 81
Daniel Schön and Stephan Menzel

[P12] A 3.75Mb Embedded RRAM IP on 40nm High-Voltage CMOS Technology 85
Yuan He, Chengxiang Ma, Xiangchao Ma, Yilong Huang, Qianze Zheng, Yue Xi, Qiumeng Wei, Jianing Li, Xiaodong He, Yongqin Wu, Weihai Bu, Kai Zheng, Jin Kang, Jianshi Tang, Bin Gao, Dong Wu, He Qian, and Huaqiang Wu

[P13] High Operation Speed (10ns/100ns) and Low Read Current (sub-1μA) 2D Floating Gate Transistor 89
Jun Yu, Jiawei Fu, Candong Zhao, Fuwei Zhuge, Qi Chen, Yuhui He, and Xiang-Shui Miao

[P14] Role of Nitrogen in Suppressing Interfacial States Generation and Improving Endurance in Ferroelectric Field Effect Transistors 93
Saifei Dai, Songwei Li, Shuangshuang Xu, Fengbin Tian, Junshuai Chai, Jiahui Duan, Wenjuan Xiong, Jinjuan Xiang, Yanrong Wang, Hao Xu, Jing Zhang, Xiaolei Wang, and Wenwu Wang

[P15] CMOS-Compatible Low-T Processing Methods for HZO-Based DRAM Capacitors by E-Field Cycling 97
Yuanbiao Li, Xinyi Tang, Guangwei Xu, Songming Miao, Xiao Chen, Jiachen Li, Di Lu, and Shibing Long

Session 4: DRAM

[4.1] 3D X-DRAM: A Novel 3D NAND-Like DRAM Cell and TCAD Simulations 101
Fu-Chang Hsu, Richard J. Huang, Re-Peng Tsay, Jui-Hsin Chang, Chia-Haur Chang, I-Wei Huang, and Kevin Hsu

[4.2] Gate-All-Around SRAM: Performance Investigation and Optimization towards Vccmin Scaling 105
Pratik B. Vyas, Ashish Pal, Gregory Costrini, Benjamin Colombeau, Bala Haran, Subi Kengeri, and El Mehdi Bazizi

[4.3] Heterogeneous Oxide Semiconductor FETs Comprising Planar FET and Vertical Channel FETs Monolithically Stacked on Si CMOS, Enabling 1-Mbit 3D DRAM 109
Hiroki Inoue, Takeya Hirose, Toshiki Mizuguchi, Yusuke Komura, Toshihiko Saito, Minato Ito, Kiyotaka Kimura, Tatsuya Onuki, Yoshinori Ando, Hiromi Sawai, Tsutomu Murakawa, Hitoshi Kunitake, Takanori Matsuzaki, Hajime Kimura, Makoto Ikeda, and Shunpei Yamazaki

[4.4] Multi-Gate Access Transistor to Minimize GIDL Leakage Current for Scaling 2-Tier Stacked $4F^2$ DRAM below Equivalent 10nm Node 113
Hang-Ting Lue, Wei-Chen Chen, Yu-Tang Lin, Keh-Chung Wang, and Chih-Yuan Lu

Session 5: NAND II

[5.1] Demonstration of High-Growth-Rate Epitaxially Grown Si Channel on 3D NAND Test Vehicle with Memory Functionality 117
Hao-Ling Tang, Insoo Jung, Frank C. C. Chin, Luc Thomas, Xin Meng, Arvind Kumar, Jaesoo Ahn, Zuoming Zhu, Abhishek Dube, and Mahendra Pakala

[5.2] Modeling and Simulation for DRAM and Flash Memory Technology Exploration and Development 121
Xi-Wei Lin, Salvatore Maria Amoroso, Ko-Hsin Lee, Meng Hsuan Ke, Tue Gunst, Pavel Tikhomirov, and Plamen Asenov

[5.3] Gate Side Injection Operating Mode for 3D NAND Flash Memories 125
L. Breuil, R. Izmailov, M. Popovici, J. Stiers, A. Arreghini, S. Ramesh, G. Van den bosch, J. Van Houdt, and M. Rosmeulen

[5.4] Design Framework for Ferroelectric Gate Stack Engineering of Vertical NAND Structures for Efficient TLC and QLC Operation 129
Dipjyoti Das, Lance Fernandes, Prasanna Venkatesan Ravindran, Taeyoung Song, Chinsung Park, Nashrah Afroze, Mengkun Tian, Hang Chen, Winston Chern, Kijoon Kim, Jongho Woo, Suhwan Lim, Kwangsoo Kim, Wanki Kim, Daewon Ha, Shimeng Yu, Suman Datta, and Asif Khan

Session 6: Embedded & RRAM

[6.1] Charge Trapping Challenges of CMOS Embedded Complementary FeFETs 133
Sven Beyer, Dominik Kleimaier, Stefan Dünkel, Halid Mulaosmanovic, Steven Soss, Johannes Müller, Zhouhang Jiang, Kai Ni, Thomas Mikolajick, and Haidi Zhou

[6.2] Improvement of MAC Accuracy using Oxygen Diffusion Barriers in Resistive Synaptic Cell Arrays 137
Youngjae Kwon, Won-Tae Koo, Sangsu Park, Dong Ik Suh, Gunhee Lee, Hyung Dong Lee, Youngbae Ahn, Dohee Kim, Seungwook Ryu, Hoseok Em, Seokjoon Kang, Chang Won Jeong, Junho Cheon, Hyejung Choi, Soo Gil Kim, Seho Lee, Jaeyun Yi, and Seon Yong Cha

[6.3] Self-Rectifying Non-Volatile Tunneling Synapse: Multiscale Modeling Augmented Development 141
B. Beltrando, M. A. Villena, A. Kumar, S. Gangopadhyay, D. Kamalanathan, E. Smith, N. Kazem, G. Saheli, S. Weeks, M. Haverty, M. Kaliappan, A. Padovani, S. Krishnan, J. Anthis, L. Larcher, and M. Pešić

[6.4] Performance and Reliability of Technology Qualified 34 Mb Split-Gate eFLASH Macro in 28 nm HKMG 145
Ralf Richter, Stefan Dünkel, Bert Müller, Frank Mauersberger, Sven Wittek, Sven Beyer, Jana Böhme, Uwe Ritter, Violetta Sessi, Zhen Xu, Maximilian Drescher, Jinho Kim, Parviz Ghazavi, Yuri Tkachev, Latt Tee, Zonglin Li, Mandana Tadayoni, Fan Luo, Nhan Do, Serguei Jourba, Catherine Decobert, Gilles Festes, Bruno Villard, and Thibaut Pate-Cazal

Session 7: Ferro

[7.1] Materials Engineering for High Performance Ferroelectric Memory 149
Ashonita Chavan, Adharsh Rajagopal, Yixin Yan, Isamu Asano, Devanarayanan Ettisserry, Vassil Antonov, Giorgio Servalli, Alessandro Calderoni, and Nirmal Ramaswamy

[7.2] A Novel 3D Gate-All-Around Vertical FeFET with Back-Gate Structure for Disturbance-Less Program Operation 153
Boncheol Ku, Jae-Min Sim, Jae Seok Hur, Jae Kyeong Jeong, Yun-Heub Song, and Changhwan Choi

[7.3] Enhanced Reliability and Trapping Behavior in Ferroelectric FETs under Cryogenic Conditions 157
Maximilian Lederer, Franz Müller, Raik Hoffmann, Ricardo Olivo, Yannick Raffel, Shouzhuo Yang, Sourav De, Roman Potjan, Oliver Ostien, Abdelrahman Altawil, Ayse Sünbül, David Lehninger, Thomas Kämpfe, and Konrad Seidel

[7.4] Charge-Based Sense Demonstration in 1T-1C HZO FeRAM Arrays to Overcome C_{BL}-Induced Bank Size Limitations 161
O. Billoint, S. Martin, J. Laguerre, L. Hosier, J. Coignus, C. Carabasse, F. Andrieu, and L. Grenouillet

Session 8: 3D Processing

[8.1] Improved 3D DRAM Design Based on Gate-Controlled Thyristor Featuring Two Asymmetrical Horizontal WL's and Vertical BL for Better Cell Size Scaling and Array Selection 165
Wei-Chen Chen, Hang-Ting Lue, Ming-Hung Wu, Yu-Tang Lin, Keh-Chung Wang, and Chih-Yuan Lu

[8.2] D2W Hybrid Bonding Challenges for HBM 169
Gaurav Mehta, Jonathan Abdilla, Raymond Hung, El Mehdi Bazizi, Yong Chang Bum, Djuro Bikajlevic, Liu Jiang, and Gregory Costrini

Author Index 173